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(FILE 'USPAT' ENTERED AT 11:38:38 ON 28 SEP 1998)  
L1 344 S AMORPHOUS(5A) (TIN OR (TITANIUM NITRIDE))  
L2 204 S AMORPHOUS(3A) (TIN OR (TITANIUM NITRIDE))  
L3 33 S AMORPHOUS(A) (TIN OR (TITANIUM NITRIDE))

FILE 'JPO' ENTERED AT 11:52:27 ON 28 SEP 1998  
L4 9 S L3

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7. 5,723,382, Mar. 3, 1998, Method of making a low-resistance contact to silicon having a titanium silicide interface, an **amorphous titanium nitride** barrier layer and a conductive plug; Gurtej S. Sandhu, et al., 438/653, 656, 657 [IMAGE AVAILABLE]

8. 5,710,070, Jan. 20, 1998, Application of titanium nitride and tungsten nitride thin film resistor for thermal ink jet technology; Lap Chan, 438/21; 347/59, 62; 438/238, 384, 648, 681 [IMAGE AVAILABLE]

11. 5,610,099, Mar. 11, 1997, Process for fabricating transistors using composite nitride structure; E. Henry Stevens, et al., 438/626, 627, 632, 635 [IMAGE AVAILABLE]

13. 5,496,762, Mar. 5, 1996, Highly resistive structures for integrated circuits and method of manufacturing the same; Gurtej S. Sandhu, et al., 438/384; 148/DIG.117, DIG.136; 438/20, 385 [IMAGE AVAILABLE]

17. 5,397,744, Mar. 14, 1995, Aluminum metallization method; Hirofumi Sumi, et al., 438/643; 148/DIG.19; 438/586, 653 [IMAGE AVAILABLE]

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